

BGA2803

MMIC wideband amplifier

Rev. 2 — 23 August 2013

Product data sheet

1. Product profile

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

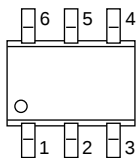
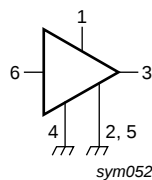
- Internally matched to $50\ \Omega$
- A gain of 23.6 dB at 950 MHz
- Output power at 1 dB gain compression = -6 dBm
- Supply current = 5.8 mA at a supply voltage of 3.0 V
- Reverse isolation > 40 dB up to 2 GHz
- Good linearity with low second order and third order products
- Noise figure = 3.6 dB at 950 MHz
- Unconditionally stable ($K > 1$)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	V _{CC}		 sym052
2, 5	GND2		
3	RF_OUT		
4	GND1		
6	RF_IN		



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGA2803	-	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 3. Marking

Type number	Marking code	Description
BGA2803	MB*	* = - : made in Hong Kong
		* = p : made in Hong Kong
		* = W : made in China
		* = t : made in Malaysia

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage	RF input AC coupled	-0.5	+4.5	V
I_{CC}	supply current		-	55	mA
P_{tot}	total power dissipation	$T_{sp} = 90\text{ °C}$	-	200	mW
T_{stg}	storage temperature		-40	+125	°C
T_j	junction temperature		-	125	°C
P_{drive}	drive power		-	-16.5	dBm

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$P_{tot} = 200\text{ mW}$; $T_{sp} = 90\text{ °C}$	300	K/W

7. Characteristics

Table 6. Characteristics

$V_{CC} = 3.3\text{ V}$; $Z_S = Z_L = 50\text{ }\Omega$; $P_i = -30\text{ dBm}$; $T_{amb} = 25\text{ °C}$; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.7	3.0	3.3	V
I_{CC}	supply current		5.0	5.8	6.6	mA

Table 6. Characteristics ...continued

$V_{CC} = 3.3\text{ V}$; $Z_S = Z_L = 50\ \Omega$; $P_i = -30\text{ dBm}$; $T_{amb} = 25\text{ }^\circ\text{C}$; measured on demo board; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$f = 250\text{ MHz}$	22.9	23.5	24.1	dB
		$f = 950\text{ MHz}$	22.9	23.6	24.3	dB
		$f = 2150\text{ MHz}$	21.2	22.6	24.1	dB
RL_{in}	input return loss	$f = 250\text{ MHz}$	9	11	13	dB
		$f = 950\text{ MHz}$	13	14	16	dB
		$f = 2150\text{ MHz}$	13	20	26	dB
RL_{out}	output return loss	$f = 250\text{ MHz}$	17	22	26	dB
		$f = 950\text{ MHz}$	12	13	14	dB
		$f = 2150\text{ MHz}$	11	14	16	dB
ISL	isolation	$f = 250\text{ MHz}$	46	66	87	dB
		$f = 950\text{ MHz}$	47	48	50	dB
		$f = 2150\text{ MHz}$	38	40	43	dB
NF	noise figure	$f = 250\text{ MHz}$	3.2	3.7	4.2	dB
		$f = 950\text{ MHz}$	3.2	3.6	4.0	dB
		$f = 2150\text{ MHz}$	3.0	3.4	3.8	dB
B_{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.5	2.7	2.9	GHz
K	Rollett stability factor	$f = 250\text{ MHz}$	18	57	95	
		$f = 950\text{ MHz}$	6	7	9	
		$f = 2150\text{ MHz}$	2	3	4	
$P_{L(sat)}$	saturated output power	$f = 250\text{ MHz}$	-4	-3	-3	dBm
		$f = 950\text{ MHz}$	-5	-3	-2	dBm
		$f = 2150\text{ MHz}$	-7	-6	-5	dBm
$P_{L(1dB)}$	output power at 1 dB gain compression	$f = 250\text{ MHz}$	-7	-6	-5	dBm
		$f = 950\text{ MHz}$	-7	-6	-4	dBm
		$f = 2150\text{ MHz}$	-9	-8	-7	dBm
$IP3_I$	input third-order intercept point	$P_{drive} = -39\text{ dBm}$ (for each tone)				
		$f_1 = 250\text{ MHz}; f_2 = 251\text{ MHz}$	-19.5	-17.5	-15.5	dBm
		$f_1 = 950\text{ MHz}; f_2 = 951\text{ MHz}$	-20.5	-18.5	-16.5	dBm
		$f_1 = 2150\text{ MHz}; f_2 = 2151\text{ MHz}$	-24.5	-20.5	-17.5	dBm
$IP3_O$	output third-order intercept point	$P_{drive} = -39\text{ dBm}$ (for each tone)				
		$f_1 = 250\text{ MHz}; f_2 = 251\text{ MHz}$	4	6	8	dBm
		$f_1 = 950\text{ MHz}; f_2 = 951\text{ MHz}$	3	5	7	dBm
		$f_1 = 2150\text{ MHz}; f_2 = 2151\text{ MHz}$	-1	+2	+5	dBm
$P_{L(2H)}$	second harmonic output power	$P_{drive} = -39\text{ dBm}$				
		$f_{1H} = 250\text{ MHz}; f_{2H} = 500\text{ MHz}$	-54	-52	-50	dBm
		$f_{1H} = 950\text{ MHz}; f_{2H} = 1900\text{ MHz}$	-46	-44	-43	dBm
$\Delta IM2$	second-order intermodulation distance	$P_{drive} = -39\text{ dBm}$ (for each tone)				
		$f_1 = 250\text{ MHz}; f_2 = 251\text{ MHz}$	33	35	37	dBc
		$f_1 = 950\text{ MHz}; f_2 = 951\text{ MHz}$	27	29	30	dBc

8. Application information

Figure 1 shows a typical application circuit for the BGA2803 MMIC. The device is internally matched to $50\ \Omega$, and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The location of the 470 pF supply decoupling capacitor (C_{dec}) can be precisely chosen for optimum performance.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.

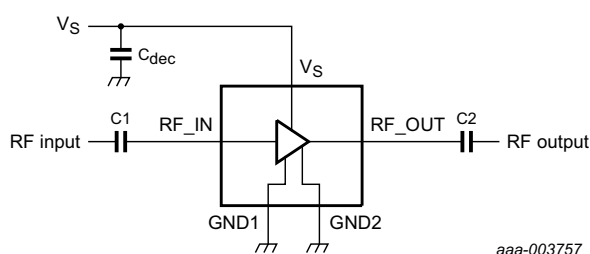
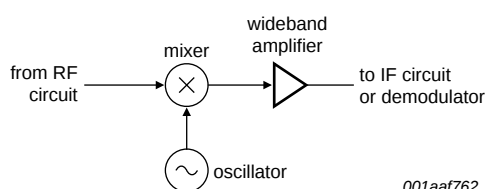


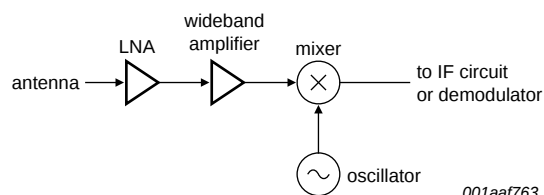
Fig 1. Typical application circuit

8.1 Application examples



The MMIC is very suitable as IF amplifier in e.g. LNB's. The excellent wideband characteristics make it an easy building block.

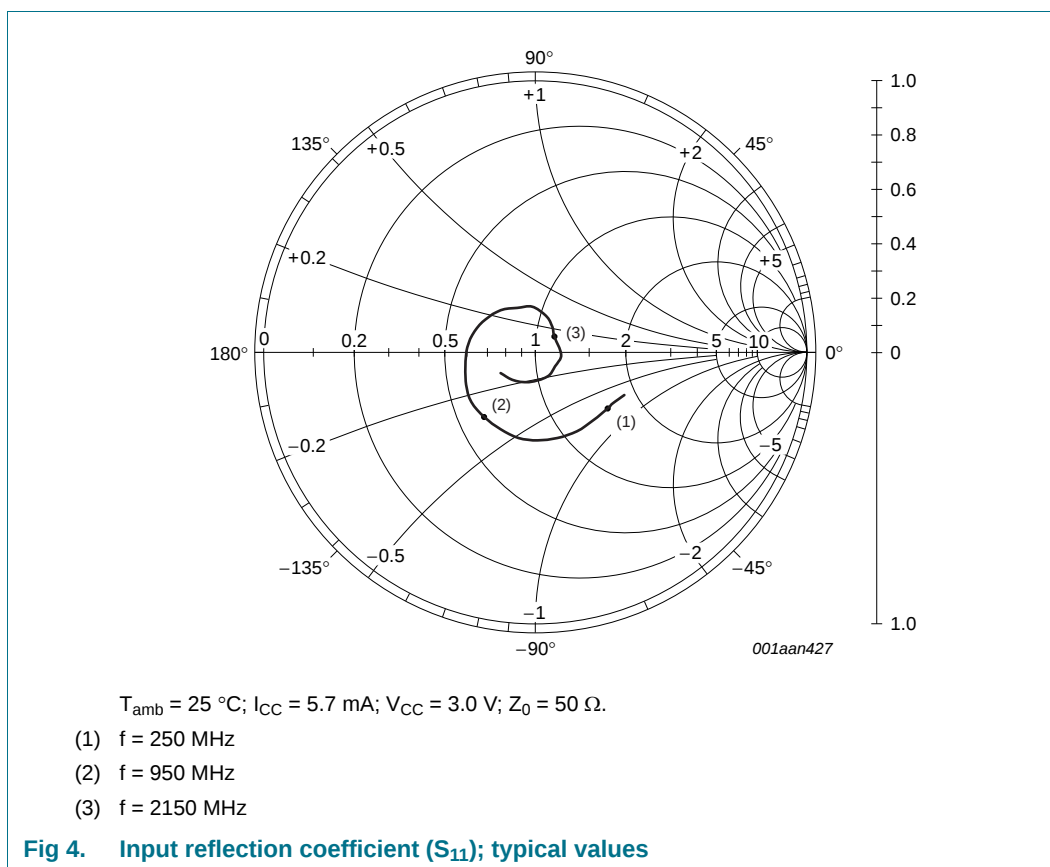
Fig 2. Application as IF amplifier

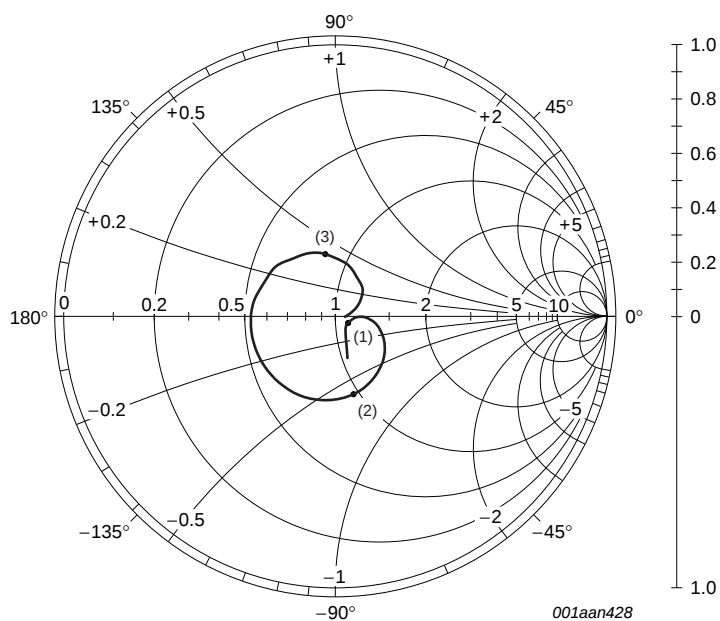


As second amplifier after an LNA, the MMIC offers an easy matching, low noise solution.

Fig 3. Application as RF amplifier

8.2 Graphs

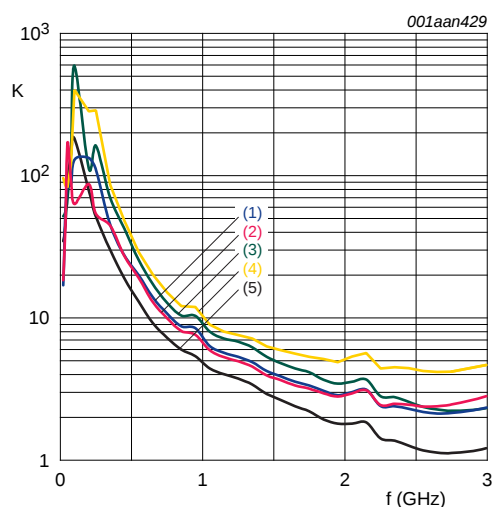




$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$; $I_{\text{CC}} = 5.7\text{ mA}$; $V_{\text{CC}} = 3.0\text{ V}$; $Z_0 = 50\text{ }\Omega$.

- (1) $f = 250\text{ MHz}$
- (2) $f = 950\text{ MHz}$
- (3) $f = 2150\text{ MHz}$

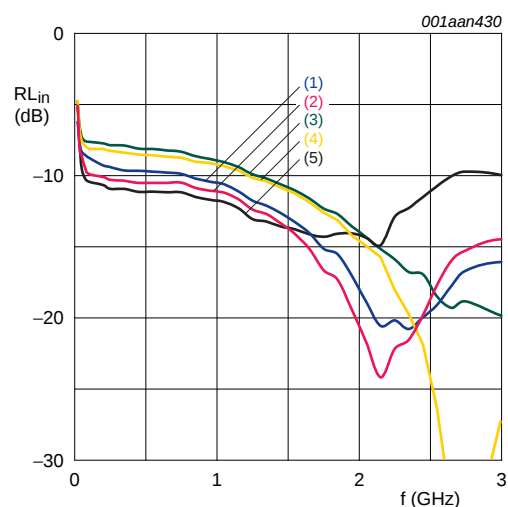
Fig 5. Output reflection coefficient (S_{22}); typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

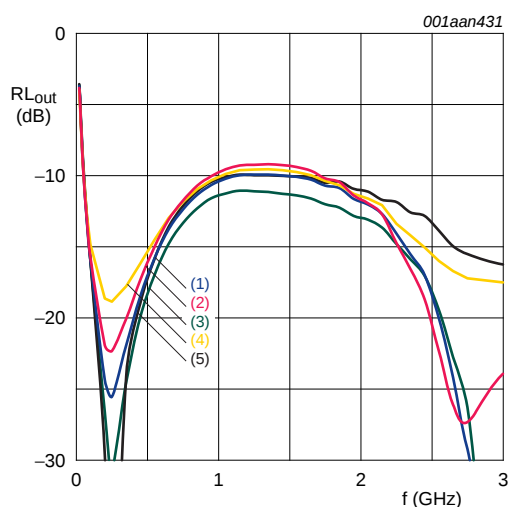
Fig 6. Rollett stability factor as function of frequency; typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

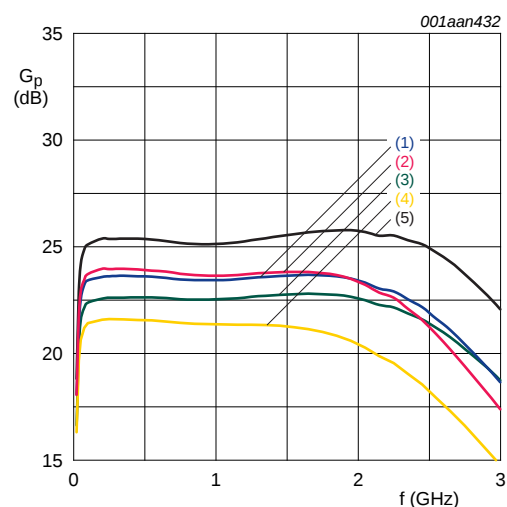
Fig 7. Input return loss as function of frequency; typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

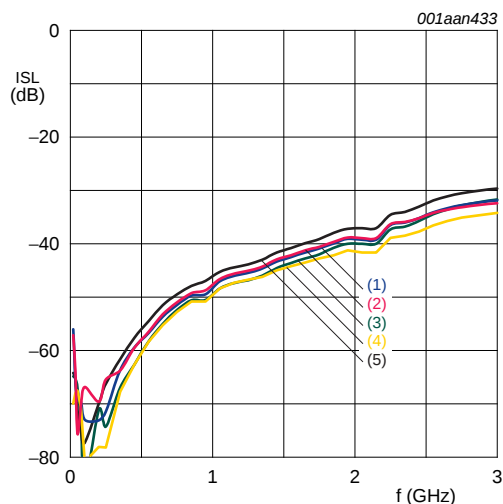
Fig 8. Output return loss as function of frequency; typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

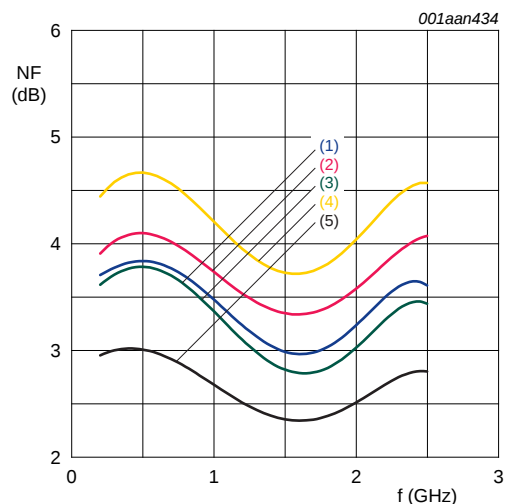
Fig 9. Power gain as function of frequency; typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

Fig 10. Isolation as function of frequency; typical values



$P_{\text{drive}} = -39 \text{ dBm}$; $Z_0 = 50 \Omega$.

- (1) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.90 \text{ mA}$
- (2) $V_{\text{CC}} = 2.7 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 4.70 \text{ mA}$
- (3) $V_{\text{CC}} = 3.0 \text{ V}$; $T_{\text{amb}} = 25 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 5.70 \text{ mA}$
- (4) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = 85 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.70 \text{ mA}$
- (5) $V_{\text{CC}} = 3.3 \text{ V}$; $T_{\text{amb}} = -40 \text{ }^\circ\text{C}$; $I_{\text{CC}} = 6.60 \text{ mA}$

Fig 11. Noise figure as function of frequency; typical values

8.3 Tables

Table 7. Supply current over temperature and supply voltages

Typical values.

Symbol	Parameter	Conditions	$T_{\text{amb}} \text{ (}^\circ\text{C)}$			Unit
			-40	+25	+85	
I_{CC}	supply current	$V_{\text{CC}} = 2.7 \text{ V}$	4.70	4.70	4.90	mA
		$V_{\text{CC}} = 3.0 \text{ V}$	5.70	5.70	5.80	mA
		$V_{\text{CC}} = 3.3 \text{ V}$	6.60	6.70	6.70	mA

Table 8. Second harmonic output power over temperature and supply voltages

Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(2H)}	second harmonic output power	f = 250 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	-49	-53	-57	dBm
		V _{CC} = 3.0 V	-49	-52	-55	dBm
		V _{CC} = 3.3 V	-50	-52	-54	dBm
		f = 950 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	-44	-46	-47	dBm
		V _{CC} = 3.0 V	-43	-44	-46	dBm
		V _{CC} = 3.3 V	-43	-44	-45	dBm

Table 9. Input power at 1 dB gain compression over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 2.7 V	-29	-28	-28	dBm
		V _{CC} = 3.0 V	-29	-28	-28	dBm
		V _{CC} = 3.3 V	-29	-28	-28	dBm
		f = 950 MHz				
		V _{CC} = 2.7 V	-28	-28	-28	dBm
		V _{CC} = 3.0 V	-28	-28	-28	dBm
		V _{CC} = 3.3 V	-28	-28	-28	dBm
		f = 2150 MHz				
		V _{CC} = 2.7 V	-29	-29	-30	dBm
		V _{CC} = 3.0 V	-29	-30	-30	dBm
		V _{CC} = 3.3 V	-29	-30	-31	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages
Typical values.

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		V _{CC} = 2.7 V	-7	-7	-8	dBm
		V _{CC} = 3.0 V	-5	-6	-6	dBm
		V _{CC} = 3.3 V	-4	-5	-5	dBm
		f = 950 MHz				
		V _{CC} = 2.7 V	-7	-7	-8	dBm
		V _{CC} = 3.0 V	-5	-6	-6	dBm
		V _{CC} = 3.3 V	-4	-4	-5	dBm
		f = 2150 MHz				
		V _{CC} = 2.7 V	-8	-9	-11	dBm
		V _{CC} = 3.0 V	-6	-8	-10	dBm
		V _{CC} = 3.3 V	-5	-7	-9	dBm

Table 11. Saturated output power over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		V _{CC} = 2.7 V	-5	-5	-5	dBm
		V _{CC} = 3.0 V	-3	-3	-4	dBm
		V _{CC} = 3.3 V	-2	-2	-3	dBm
		f = 950 MHz				
		V _{CC} = 2.7 V	-4	-5	-5	dBm
		V _{CC} = 3.0 V	-3	-3	-4	dBm
		V _{CC} = 3.3 V	-2	-2	-3	dBm
		f = 2150 MHz				
		V _{CC} = 2.7 V	-5	-7	-9	dBm
		V _{CC} = 3.0 V	-4	-6	-7	dBm
		V _{CC} = 3.3 V	-3	-5	-7	dBm

Table 12. Second-order intermodulation distance over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
ΔIM2	second-order intermodulation distance	f ₁ = 250 MHz; f ₂ = 251 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	29	34	40	dBc
		V _{CC} = 3.0 V	32	35	39	dBc
		V _{CC} = 3.3 V	33	36	39	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	27	28	28	dBc
		V _{CC} = 3.0 V	29	29	28	dBc
		V _{CC} = 3.3 V	30	30	30	dBc

Table 13. Output third-order intercept point over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
IP _{3O}	output third-order intercept point	f ₁ = 250 MHz; f ₂ = 251 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	5	4	3	dBm
		V _{CC} = 3.0 V	7	6	5	dBm
		V _{CC} = 3.3 V	8	7	6	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	4	3	3	dBm
		V _{CC} = 3.0 V	6	5	4	dBm
		V _{CC} = 3.3 V	8	7	5	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz; P _{drive} = -39 dBm				
		V _{CC} = 2.7 V	2	0	-1	dBm
		V _{CC} = 3.0 V	3	2	-1	dBm
		V _{CC} = 3.3 V	4	2	0	dBm

Table 14. -3 dB bandwidth over temperature and supply voltages*Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
B _{-3dB}	-3 dB bandwidth	V _{CC} = 2.7 V	2.770	2.591	2.382	GHz
		V _{CC} = 3.0 V	2.837	2.651	2.446	GHz
		V _{CC} = 3.3 V	2.892	2.702	2.490	GHz

9. Test information

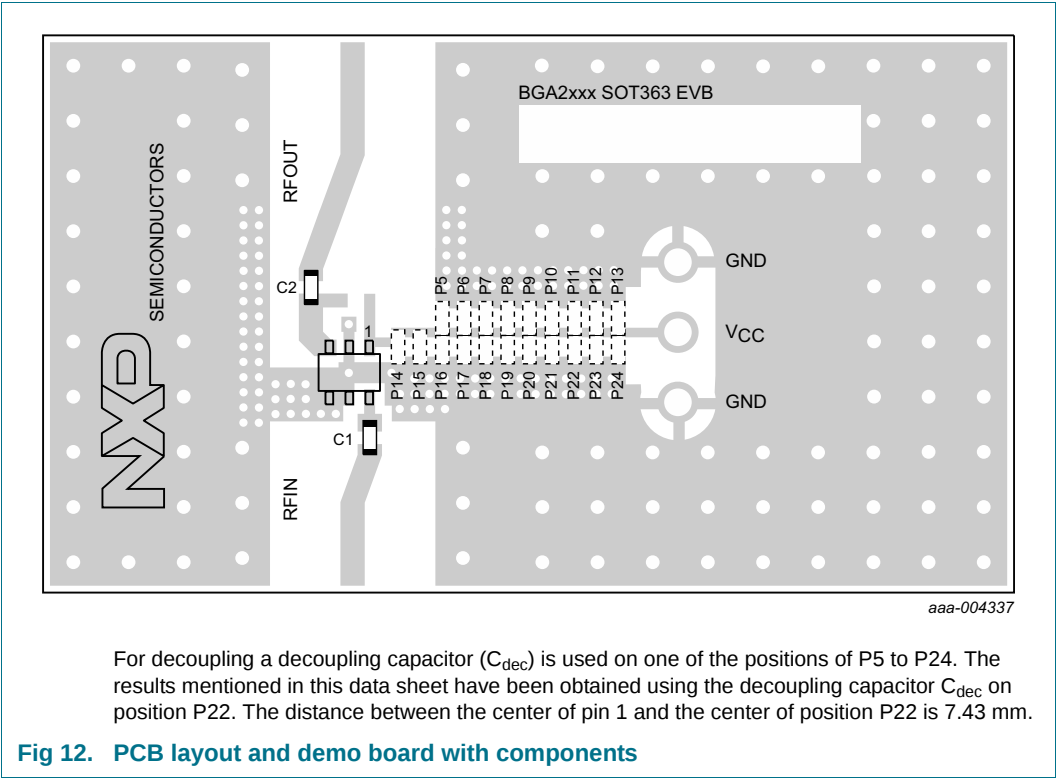


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions	Remarks
C1, C2	multilayer ceramic chip capacitor	470 pF	0603	X7R RF coupling capacitor
P5 to P24 [1]	position for multilayer ceramic chip capacitor C_{dec}	470 pF	0603	X7R RF decoupling capacitor
IC1	BGA2803 MMIC	-	SOT363	

[1] For decoupling a decoupling capacitor (C_{dec}) is used on one of the positions of P5 to P24. The results mentioned in this data sheet have been obtained using the decoupling capacitor C_{dec} on position P22.

10. Package outline

Plastic surface-mounted package; 6 leads SOT363

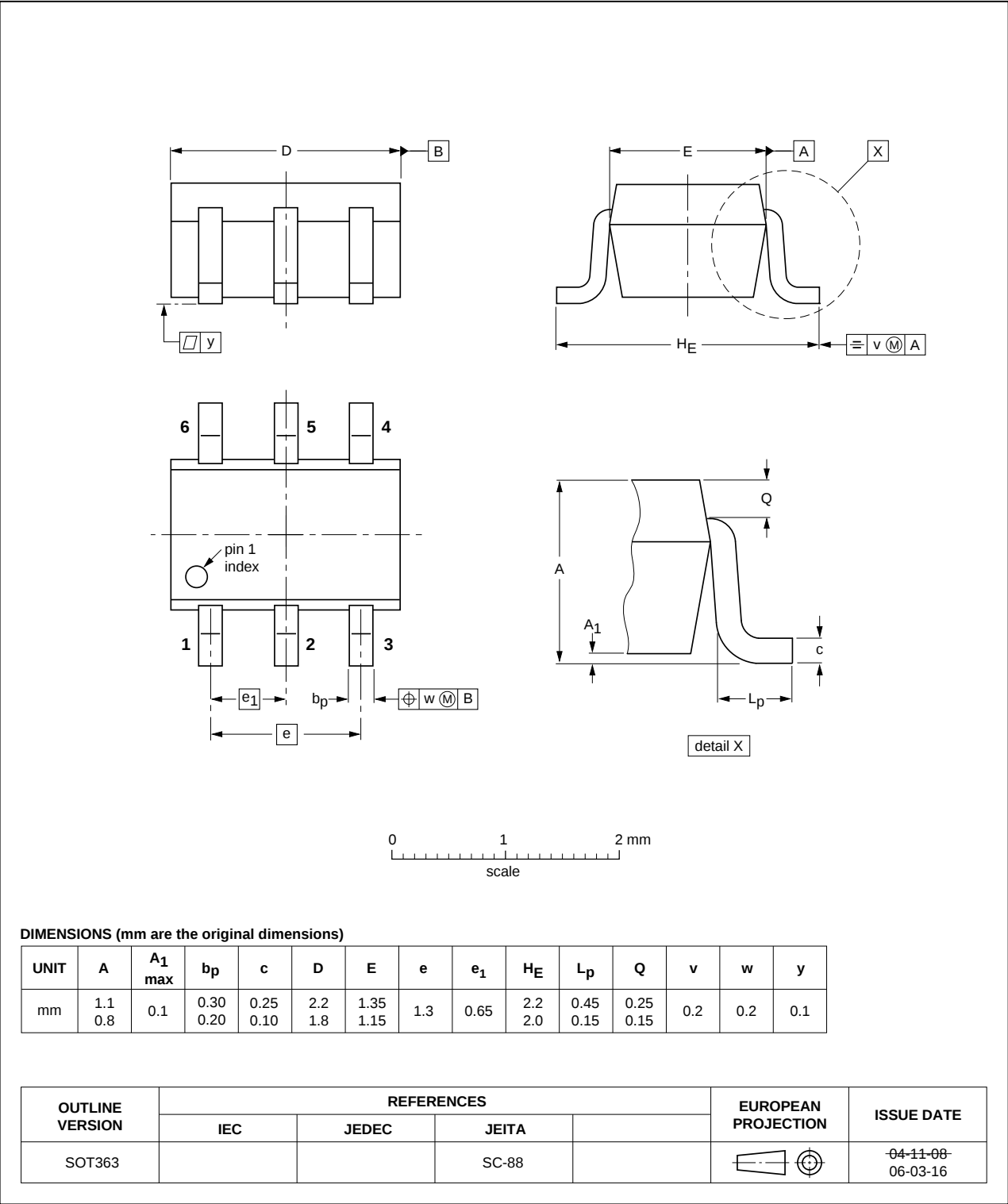


Fig 13. Package outline SOT363

11. Abbreviations

Table 16. Abbreviations

Acronym	Description
IF	Intermediate Frequency
LNA	Low-Noise Amplifier
LNB	Low-Noise Block converter
PCB	Printed-Circuit Board
SMD	Surface Mounted Device

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA2803 v.2	20130823	Product data sheet	-	BGA2803 v.1
Modifications	• Section 1.2 on page 1: section has been updated • Table 4 on page 2: the maximum value for V_{CC} has been changed to 4.5 V • Table 6 on page 2: table has been updated • Section 8 on page 4: second paragraph has been updated • Figure 1 on page 4: figure has been changed • Table 14 on page 12: table has been updated • Figure 12 on page 13: figure has been replaced • Table 15 on page 13: table has been replaced			
BGA2803 v.1	20110429	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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